

2D AND TOPOLOGICAL MAGNETIC MATERIALS

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Two dimensional (2D) magnets and heterostructures with topological insulators (TI) present new opportunities for energy-efficient spintronic devices due to their low magnetic volume, high spin-torque efficiency, novel quantum states, and interfacial proximity effects. Our focus is to develop robust room temperature 2D magnets, to understand the electronic, chemical, and magnetic interactions at 2D magnet-TI interfaces, and to realize spintronic functionality and novel magnetic topological states. Here, we describe our work utilizing molecular beam epitaxy for precise, atom-by-atom deposition of van der Waals materials consisting of MnSe₂, Bi₂Se₃, and MnBi₂Se₄. Starting with the epitaxial growth of MnSe₂ on GaSe and SnSe₂ base layers, we observed room temperature ferromagnetism in the monolayer limit [1]. Subsequent integration of MnSe₂ onto the topological insulator Bi₂Se₃ revealed chemical migration and dipole formation at the interface [2]. Specifically, we learned of the propensity for the MnSe₂ to intermix with the underlying Bi₂Se₃ to form a MnBi₂Se₄ septuple layer. By repeating the deposition of a Bi₂Se₃ followed by MnSe₂, we synthesized multilayer MnBi₂Se₄ for the first time (Figure 1a) [3]. This material is the cousin of the well-studied MnBi₂Te₄, a magnetic topological insulator exhibiting quantum anomalous Hall effect and axion insulator state. Angle-resolved photoemission spectroscopy of our MnBi₂Se₄ shows the presence of a topological Dirac surface state (Figure 1b). Magnetic measurements provide evidence of a layered antiferromagnetic state, similar to that observed in MnBi₂Te₄, but with an in-plane orientation of the magnetic moments which could give rise to alternative topological states.

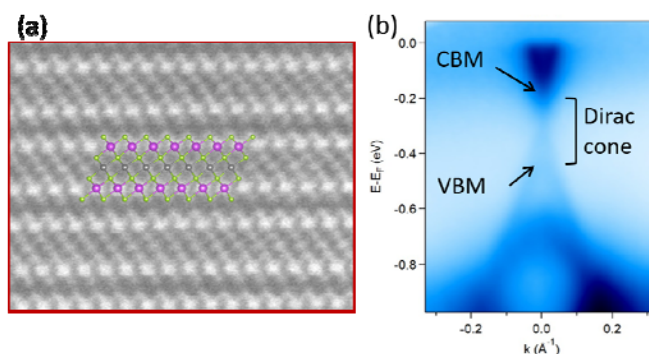


Figure 1. (a) TEM image of MnBi₂Se₄. (b) ARPES showing topological Dirac surface state.

References

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